

SIDC32D170H

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 1700V EMCON 3 technology 200 μm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

EUPEC power modules



Applications:

· resonant applications, drives

Chip Type	V _R	I _F	Die Size	Package	Ordering Code
SIDC32D170H	1700V	50A	5.7 x 5.7 mm ²	sawn on foil	Q67050-A4174- A001

MECHANICAL PARAMETER:

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Raster size	5.7 x 5.7				
Area total / active	32.49 / 22.41	mm ²			
Anode pad size	3.68 x 3.68				
Thickness	200	μm			
Wafer size	150	mm			
Flat position	180	deg			
Max. possible chips per wafer	442 pcs				
Passivation frontside	Photoimide				
Anode metallization	3200 nm Al Si Cu				
Cathode metallization	Ni Ag -system suitable for epoxy and soft solder die bonding				
Die bond	electrically conductive glue or solder				
Wire bond	AI, ≤500μm				
Reject Ink Dot Size Ø 0.65mm; max 1.2mm					
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C				



SIDC32D170H

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		1700	٧
Continuous forward current limited by T_{jmax}	I _F		50	
Single pulse forward current (depending on wire bond configuration)	I _{FSM}	t _P = 10 ms sinusoidal	310	А
Maximum repetitive forward current limited by T _{jmax}	I _{FRM}		100	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-55+150	°C

$\textbf{Static Electrical Characteristics} \text{ (tested on chip)}, \ \textit{T}_{j}\text{=25 °C, unless otherwise specified}$

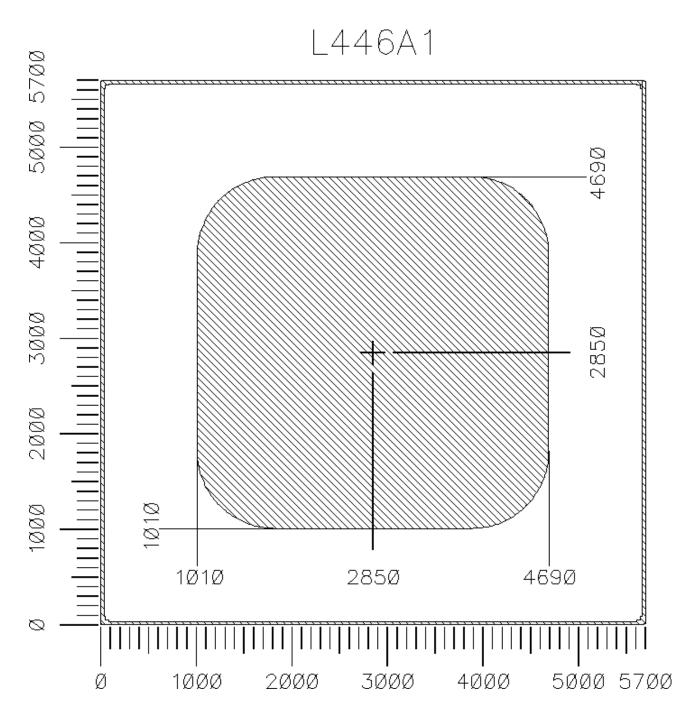
Parameter	Symbol	Condi	Value			Unit	
raiametei	Symbol	Conditions		min.	Тур.	max.	
Reverse leakage current	I _R	$V_R = 1700 V$	<i>T_j=25°C</i>			27	μΑ
Cathode-Anode breakdown Voltage	V_{Br}	I _R =0.25mA	$T_j=25^{\circ}C$	1700			V
Forward voltage drop	V_F	I _F =50A	<i>T_j</i> =25° <i>C</i>		1.8		V

Dynamic Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
raiailletei	Syllibol			min.	Тур.	max.	Oiiit
Peak recovery current	I_{RRM1}	$I_F=50A$	$T_j = 25 ^{\circ}C$		62		Α
	I _{RRM2}	$di/dt=730 A/\mu s$ $V_R=900 V$	$T_j = 125 ^{\circ}C$		67		
Reverse recovery charge	Q_{rr1}	I _F =50A di/dt=730A/μs	$T_j=25^{\circ}C$		13.3		μC
	Q_{rr2}	$V_R = 900V$	T _j =125° C		21.7		μΟ
Reverse recovery energy	E _{rec1}	I _F =50A	$T_{\rm j}$ = 25° C		6.7		
	E _{rec2}	di/dt=730A/μs V _R =900V	T _j =125° C		11.7		mJ



CHIP DRAWING:





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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the	INFINEON TECHNOLOGIES /	tbd
device data sheet	EUPEC	ibu

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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